



P0130AA

SENSITIVE

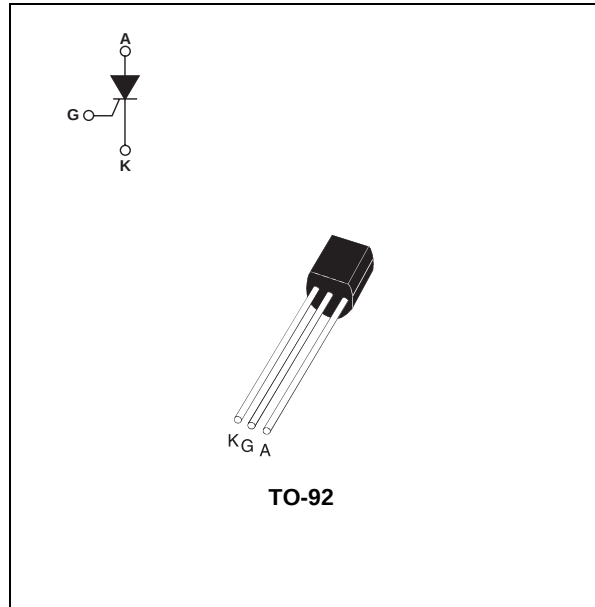
0.8A SCRs

MAIN FEATURES:

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	100	V
I_{GT}	1	μA

DESCRIPTION

The P0130AA is a gate sensitive SCR, packaged in TO-92, used in conjunction of a TN22 A.S.D™ and of a resistor in electronic starter for fluorescent tubelamps.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)		$T_I = 55^{\circ}C$	0.8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)		$T_I = 55^{\circ}C$	0.5	A
I_{TSM}	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	$T_j = 25^{\circ}C$	8	A
		$t_p = 10 \text{ ms}$		7	
I^2t	I^2t Value for fusing	$t_p = 10 \text{ ms}$	$T_j = 25^{\circ}C$	0.24	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^{\circ}C$	50	$A/\mu s$
I_{GM}	Peak gate current	$t_p = 20 \mu s$	$T_j = 125^{\circ}C$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^{\circ}C$	0.1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^{\circ}C$

P0130AA**ELECTRICAL CHARACTERISTICS** ($T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions			P0130AA	Unit
I_{GT}	$V_D = 12\text{ V}$ $R_L = 140\ \Omega$	MIN.		0.1	μA
				1	
V_{GT}		MAX.		0.8	V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $R_{GK} = 1\text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN.	0.1	V
V_{RG}	$I_{RG} = 10\ \mu\text{A}$		MIN.	8	V
I_H	$I_T = 50\text{ mA}$ $R_{GK} = 1\text{ k}\Omega$		MAX.	5	mA
I_L	$I_G = 1\text{ mA}$ $R_{GK} = 1\text{ k}\Omega$		MAX.	6	mA
dV/dt	$V_D = 67\ \% V_{DRM}$ $R_{GK} = 1\text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN.	25	V/ μs
V_{TM}	$I_{TM} = 1.6\text{ A}$ $t_p = 380\ \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.95	V
V_{t0}	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	0.95	V
R_d	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	600	$\text{m}\Omega$
I_{DRM}	$V_{DRM} = V_{RRM}$ $R_{GK} = 1\text{ k}\Omega$	$T_j = 25^\circ\text{C}$	MAX.	1	μA
I_{RRM}		$T_j = 125^\circ\text{C}$	MAX.	100	

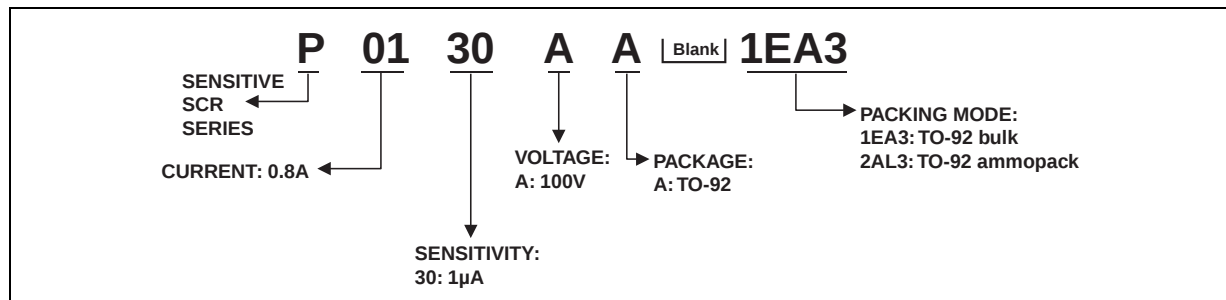
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-i)}$	Junction to case (DC)	80	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient (DC)	150	$^\circ\text{C}/\text{W}$

PRODUCT SELECTOR

Part Number	Voltage	Sensitivity	Package
P0130AA	100V	1 μA	TO-92

ORDERING INFORMATION



OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing mode
P0130AA 1EA3	P0130AA	0.2 g	2500	Bulk
P0130AA 2AL3	P0130AA	0.2 g	2000	Ampack

Note: xx = sensitivity, y = voltage

Fig. 1: Maximum average power dissipation versus average on-state current.

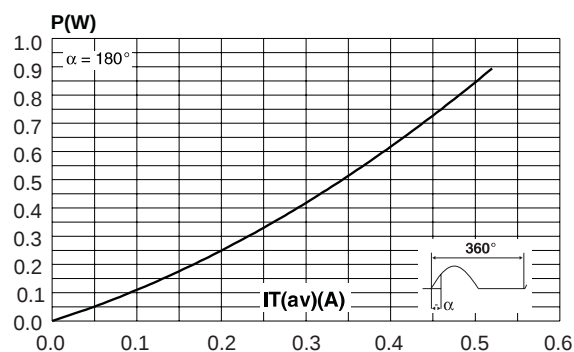


Fig. 2-2: Average and D.C. on-state current versus ambient temperature.

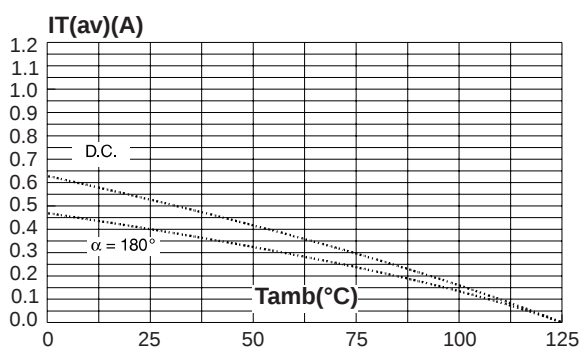


Fig. 2-1: Average and D.C. on-state current versus lead temperature.

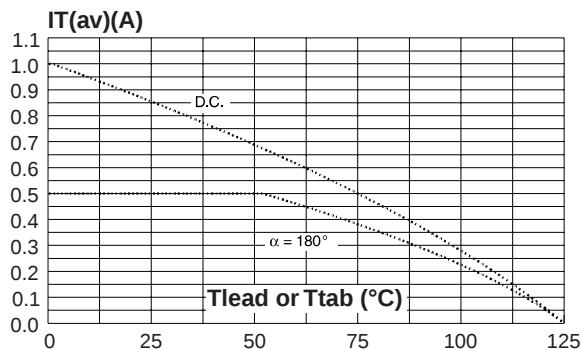


Fig. 3: Relative variation of thermal impedance junction to ambient versus pulse duration.

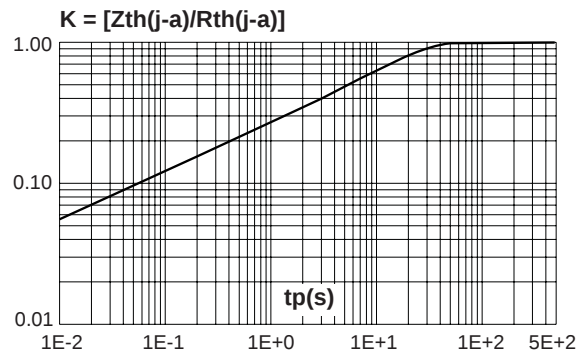


Fig. 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

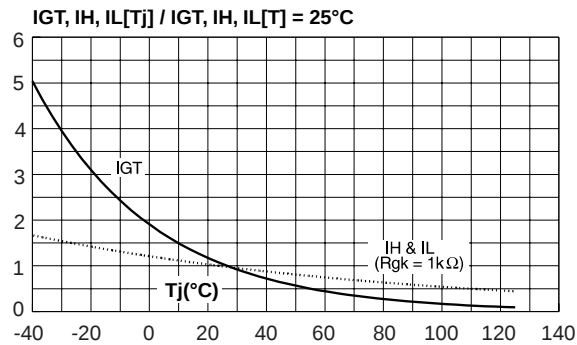


Fig. 6: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).

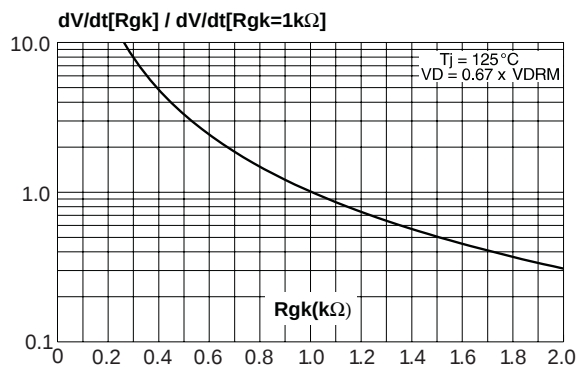


Fig. 8: Surge peak on-state current versus number of cycles.

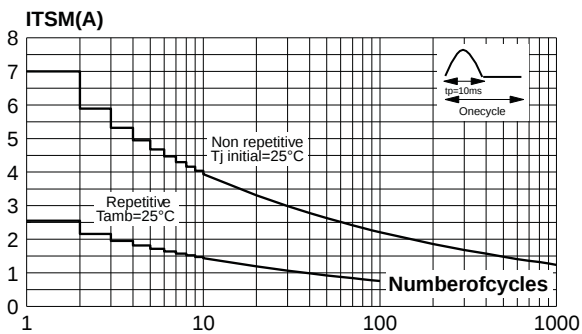


Fig. 5: Relative variation of holding current versus gate-cathode resistance (typical values).

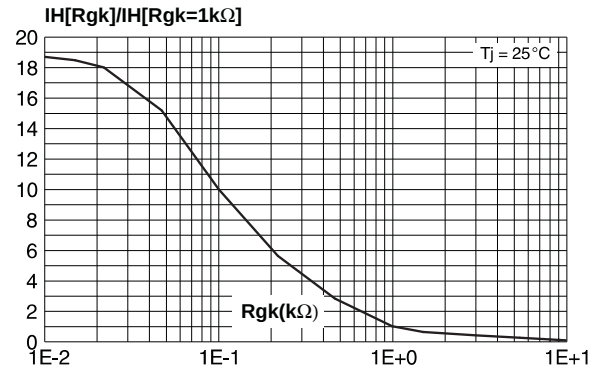


Fig. 7: Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values).

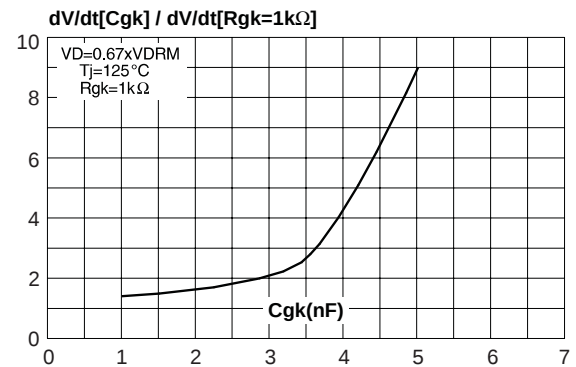


Fig. 9: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ ms}$, and corresponding value of I^2t .

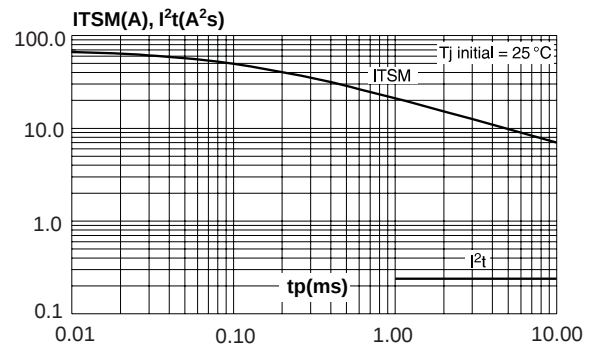
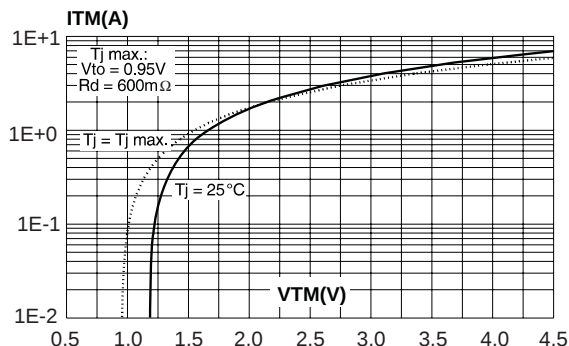
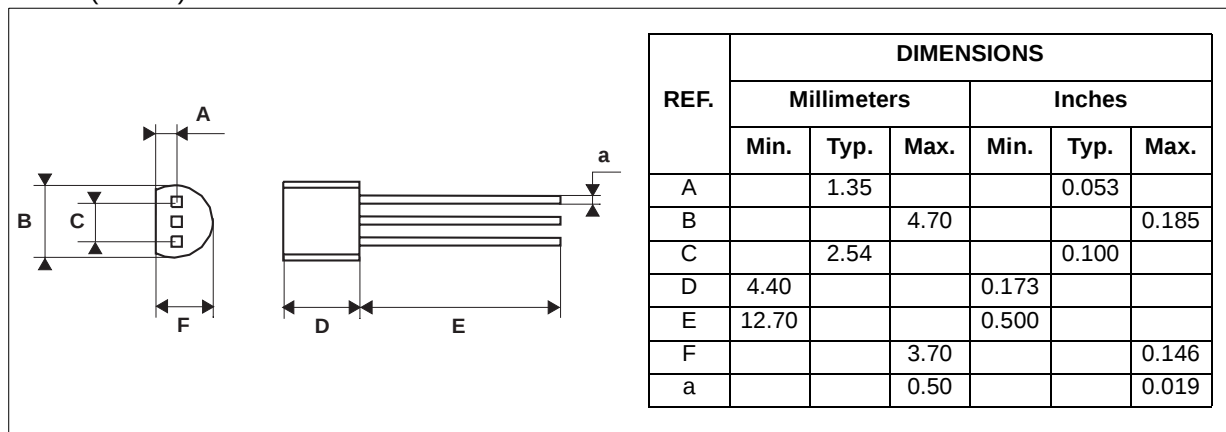


Fig. 10: On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO-92 (Plastic)



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